

# MA3XD15

## Silicon epitaxial planar type

For rectification

For protection against reverse current

### ■ Features

- Mini type 3-pin package
- Low  $V_F$  or Low  $I_R$  type:  $V_F < 0.45$  V,  $I_R < 100$   $\mu$ A
- Allowing to rectify under ( $I_{F(AV)} = 1$  A) condition

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	20	V
Repetitive peak reverse voltage	$V_{RRM}$	25	V
Non-repetitive peak forward surge current*1	$I_{FSM}$	3	A
Average forward current*2	$I_{F(AV)}$	1.0	A
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

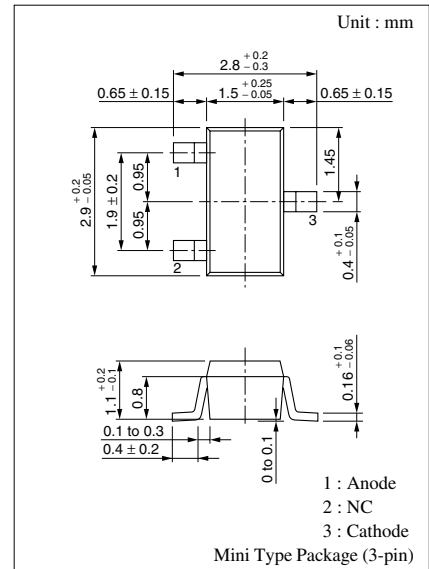
Note) \*1: The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

\*2: With a alumina PC board

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 20$ V			100	$\mu$ A
Forward voltage (DC)	$V_F$	$I_F = 1.0$ A			0.45	V
Terminal capacitance	$C_t$	$V_R = 0$ V, $f = 1$ MHz		120		pF

Note) Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.



Marking Symbol: M5N

Internal Connection

